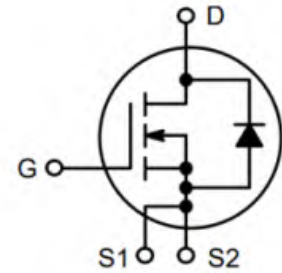


Features

- High blocking voltage with low on-resistance
- High-speed switching with low capacitances
- Low Switching Losses
- Sense pin for optimized switching performance
- RoHS compliant with Halogen-free

HF

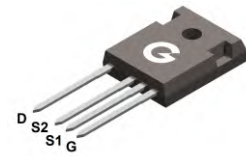


Applications

- Solar inverters
- Charger
- Uninterruptible Power Supply
- Switch Mode Power Supplies

Mechanical Data

- Case: TO-247-4L
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



TO-247-4L

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
GSC170R022U4	TO-247-4L	30 pcs / Tube	GSC170R022U4

Maximum Ratings

(@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	1700	V
Gate-to-Source Voltage (transient)	V_{GSS}	-8/+22	V
Gate-to-Source Voltage (static)		-4/+18	V
Continuous Drain Current ($T_C = 25^\circ\text{C}$)	I_D	123	A
Continuous Drain Current ($T_C = 100^\circ\text{C}$)		78	A
Pulsed Drain Current	I_{DM}	260	A
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	625	W
Operating Junction Temperature Range	T_J	-40 ~ +175	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-40 ~ +175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	-	0.24		$^\circ\text{C}/\text{W}$

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 100\mu A$	1700	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 1700V, V_{GS} = 0V$	-	1	-	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS} = 18V, V_{DS} = 0V$	-	-	250	nA
		$V_{GS} = -4V, V_{DS} = 0V$	-	-	-100	nA
On Characteristics						
$R_{DS(ON)}$	Drain-Source On-resistance *1	$V_{GS} = 18V, I_D = 80A, T_J = 25^\circ\text{C}$	-	22	-	m Ω
		$V_{GS} = 18V, I_D = 80A, T_J = 150^\circ\text{C}$	-	30	-	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 20mA$	2	-	4	V
R_G	Gate Resistance	$V_{GS} = 0V, f = 1MHz$	-	4.4	-	Ω
Dynamic Characteristics						
C_{ISS}	Input Capacitance	$V_{DS} = 1200V$ $V_{GS} = 0V$ $f = 100kHz$	-	5133	-	pF
C_{OSS}	Output Capacitance					
C_{RSS}	Reverse Transfer Capacitance					
Switching Characteristics						
$t_{d(ON)}$	Turn-on Delay Time *2	$V_{DD} = 1200V$ $V_{GS} = -4/18V$ $I_D = 50A$ $R_G = 2.5\Omega$	-	28	-	ns
t_r	Turn-on Rise Time *2					
$t_{d(OFF)}$	Turn-Off Delay Time *2					
t_f	Turn-Off Fall Time *2					
E_{on}	Turn-On Energy *2		-	1541	-	μJ
E_{off}	Turn-Off Energy *2		-	565	-	
Q_G	Total Gate-Charge	$V_{DD} = 1200V$	-	207	-	nC
Q_{GS}	Gate to Source Charge	$V_{GS} = -4/18V$	-	65	-	
Q_{GD}	Gate to Drain (Miller) Charge	$I_D = 50A$	-	49	-	
Source-Drain Diode Characteristics						
V_{SD}	Diode Forward Voltage *1	$I_{SD} = 40A, V_{GS} = -4V, T_J = 25^\circ\text{C}$	-	4.4	-	V
		$I_{SD} = 40A, V_{GS} = -4V, T_J = 150^\circ\text{C}$	-	3.9	-	
t_{rr}	Reverse Recovery Time	$I_F = 50A, V_R = 1200V$	-	16	-	ns
Q_{rr}	Reverse Recovery Charge	$d_i/d_t = 3506A/\mu s$	-	228	-	nC

Notes:

- The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

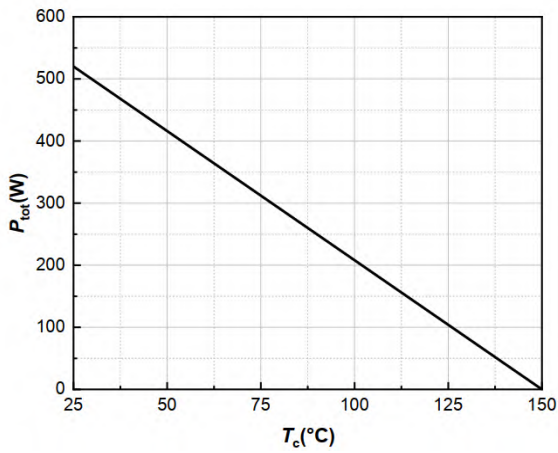


Fig 1 Power Dissipation

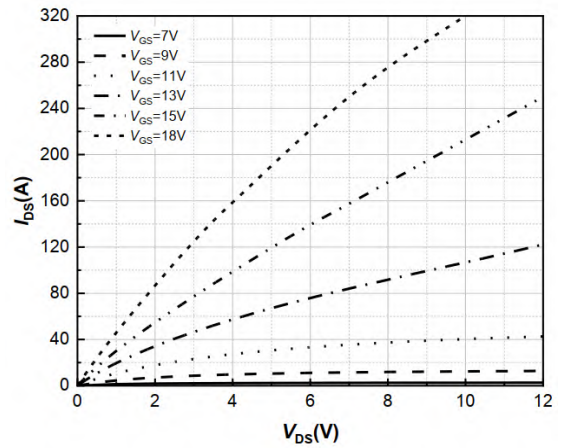


Fig 2 Typical Output Characteristics ($T_J = -40^\circ\text{C}$)

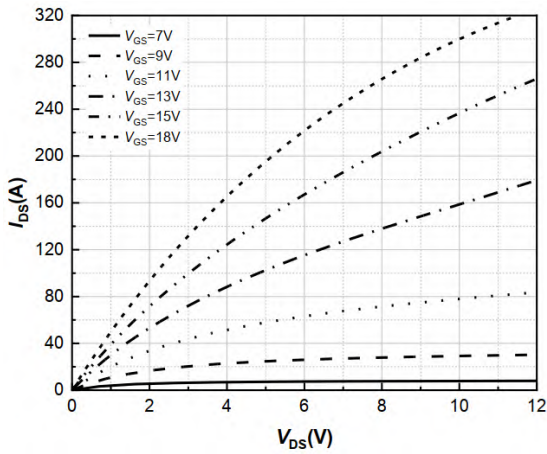


Fig 3 Typical Output Characteristics ($T_J = 25^\circ\text{C}$)

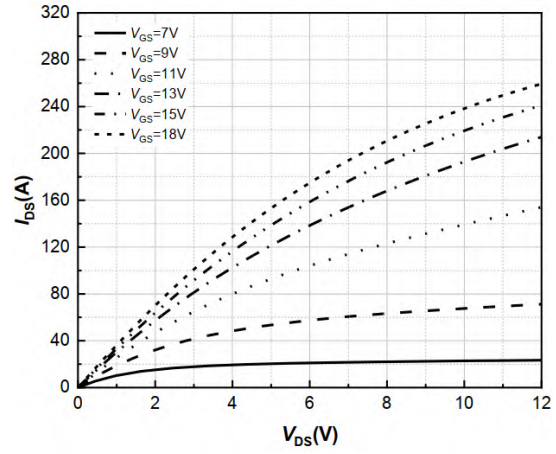


Fig 4 Typical Output Characteristics ($T_J = 150^\circ\text{C}$)

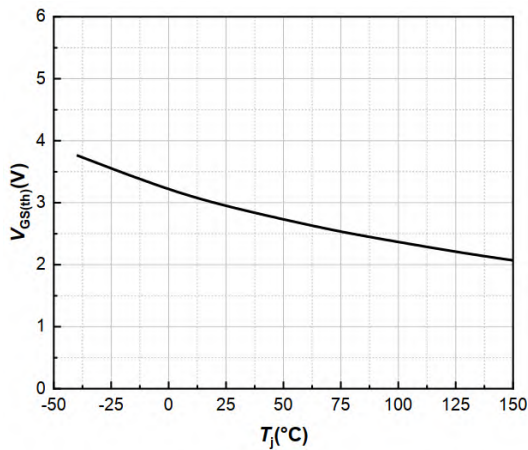


Fig 5 $V_{GS(th)}$ vs. Junction Temperature

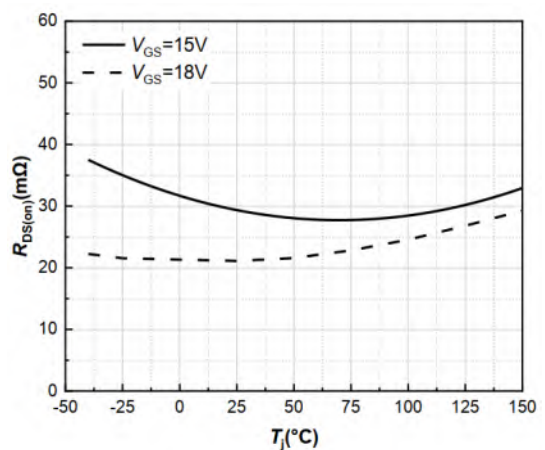


Fig 6 On-Resistance vs. Junction Temperature

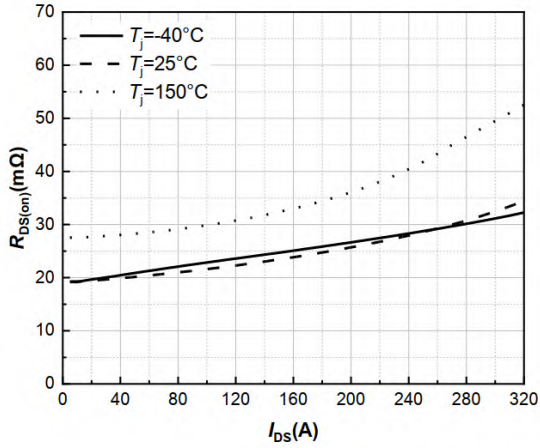


Fig 7 On-Resistance vs. Drain Current

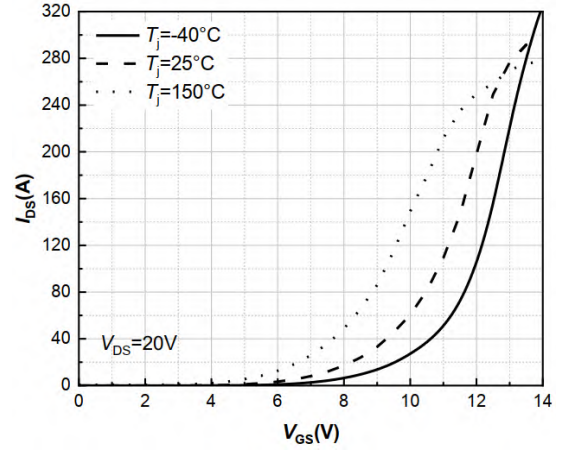


Fig 8 Transfer Characteristics

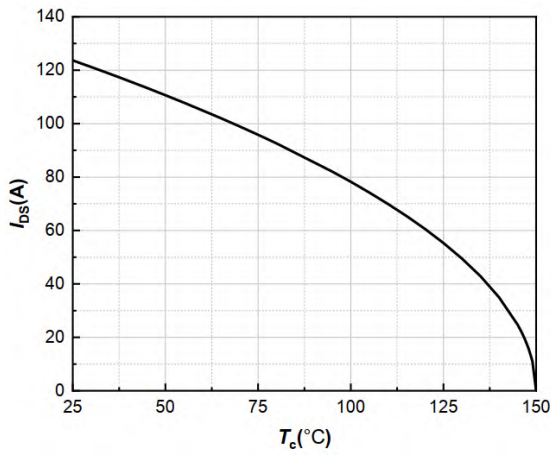


Fig 9 Diode Forward Voltage vs. Junction Temperature

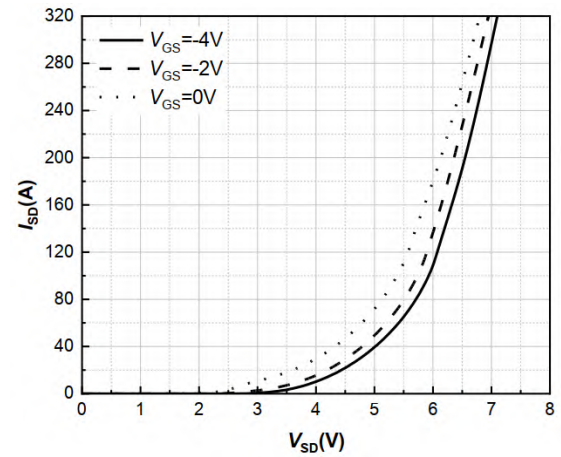


Fig 10 Body-Diode Characteristics ($T_J = -40^\circ\text{C}$)

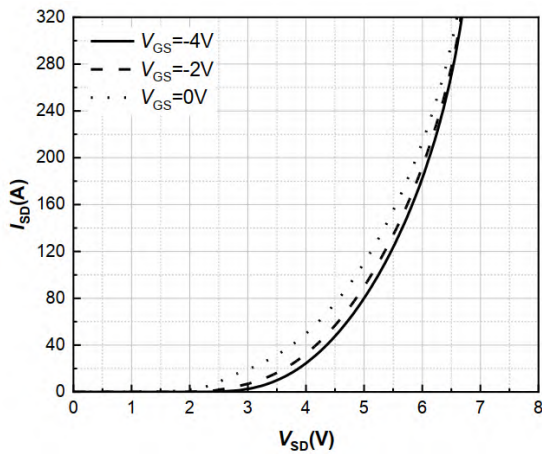


Fig 11 Body-Diode Characteristics ($T_J = 25^\circ\text{C}$)

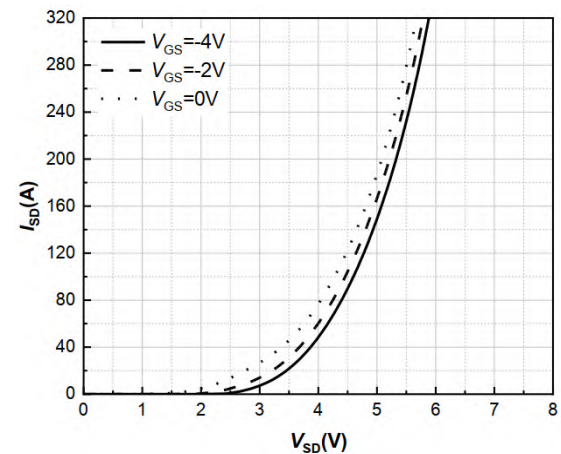


Fig 12 Body-Diode Characteristics ($T_J = 150^\circ\text{C}$)

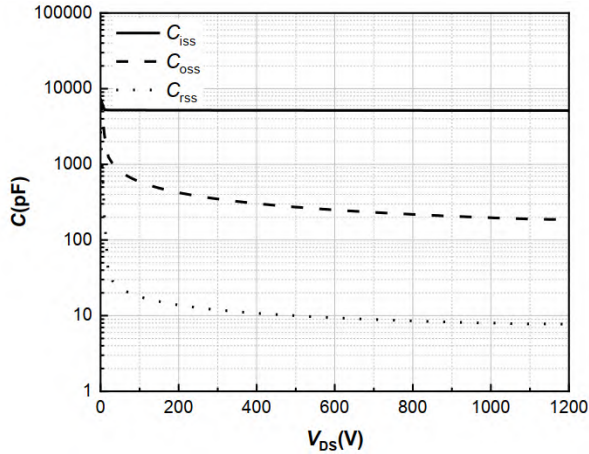


Fig 13 Capacitance Characteristics

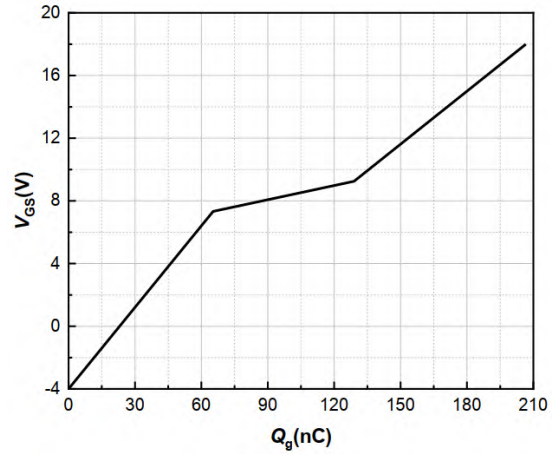


Fig 14 Gate-Charge Characteristics

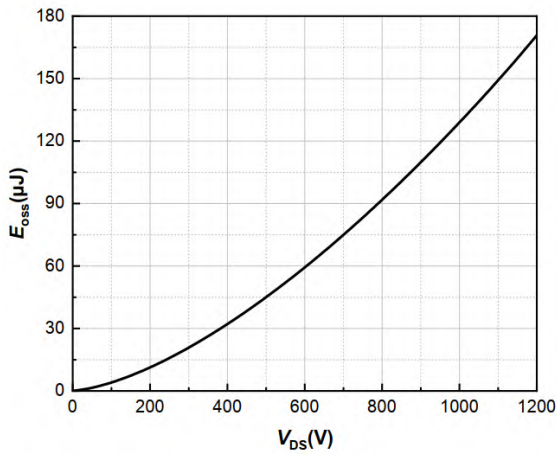


Fig 15 Output Capacitor Stored Energy

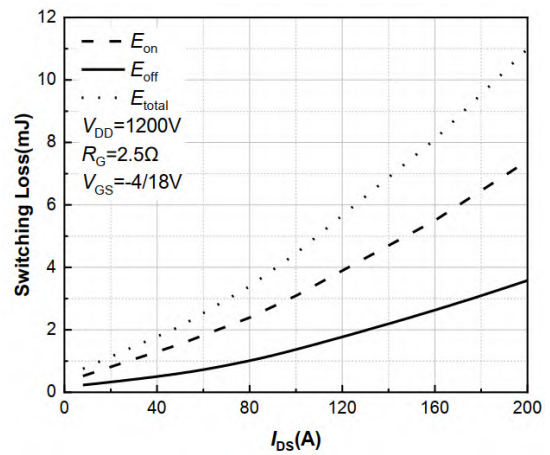


Fig 16 Clamped Inductive Switching Energy vs. Drain Current

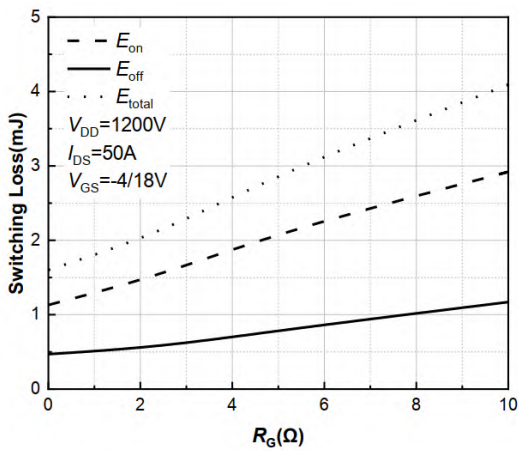


Fig 17 Clamped Inductive Switching Energy vs. R_G

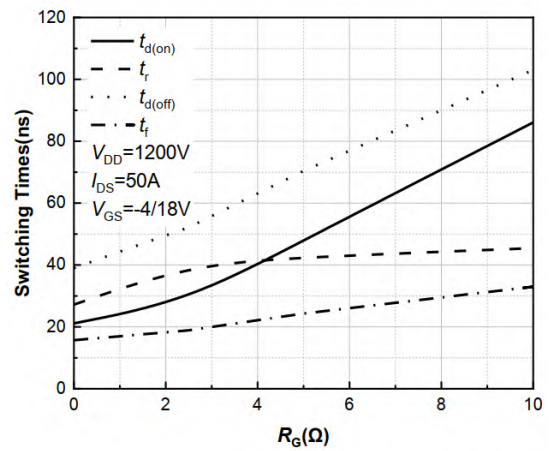


Fig 18 Switching Times vs. R_G

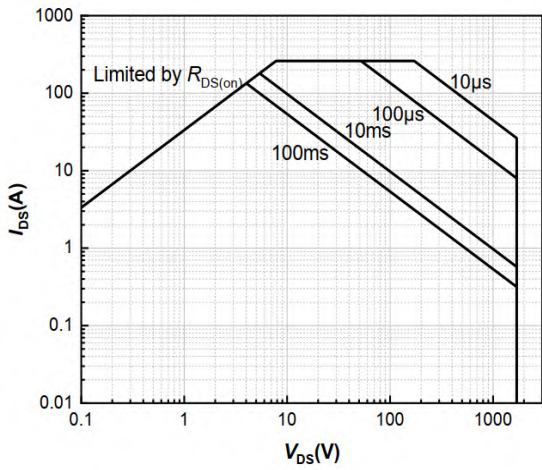


Fig 19 Safe Operating Area

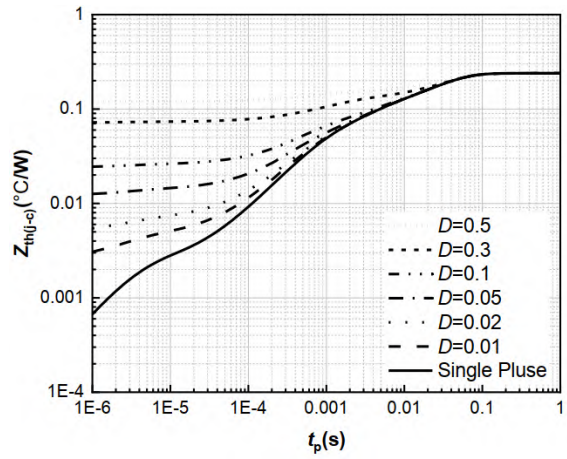


Fig 20 Maximum transient thermal impedance

Package Outline Dimensions (Unit: mm)

